AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claims 1-17 (Cancelled)

18. (Currently Amended) An in-plane switching mode liquid crystal display (LCD) device comprising:

a gate electrode on a substrate;

a gate insulating film on an entire surface of the substrate;

a semiconductor layer and an ohmic contact layer on the gate insulating film;

a buffer layer on the ohmic contact layer;

a pixel electrode on the buffer layer;

source or drain electrodes on the pixel electrode, the source or drain electrodes being connected with the pixel electrode [[on]] at an overlap of the source or drain electrodes and an end portion of the buffer layer;

a passivation layer on the pixel electrode; and

a common electrode on the passivation layer substantially parallel to the pixel electrode.

19. (Original) The in-plane switching mode LCD device as claimed in claim 18, wherein the gate electrode includes a low resistance material.

20. (Original) The in-plane switching mode LCD device as claimed in claim 19, wherein the low resistance material includes one of aluminum (Al), copper (Cu), and silver (Ag).

21. (Original) The in-plane switching mode LCD device as claimed in claim 18, wherein the buffer layer includes a metal.

22. (Original) The in-plane switching mode LCD device as claimed in claim 21, wherein the buffer layer includes titanium (Ti).

23. (Original) The in-plane switching mode LCD device as claimed in claim 18, wherein the source and drain electrodes include a low resistance material.

24. (Original) The in-plane switching mode LCD device as claimed in claim 23, wherein the low resistance material includes one of aluminum (Al), copper (Cu), and silver (Ag).

25. (Original) The in-plane switching mode LCD device as claimed in claim 18, wherein the pixel electrode includes transparent conductive material.

26. (Original) The in-plane switching mode LCD device as claimed in claim 25, wherein the pixel electrode includes indium tin oxide.

27. (Original) The in-plane switching mode LCD device as claimed in claim 18, wherein the common electrode includes indium tin oxide.

28. (Currently Amended) A method for manufacturing an in-plane switching mode liquid crystal display (LCD) device comprising:

forming a gate electrode on a substrate;

forming a gate insulating film, a semiconductor layer, an ohmic contact layer, and a buffer layer on the gate electrode;

forming a pixel electrode on the buffer layer;

forming a source electrode or a drain electrode on the pixel electrode, the source [[and]] or drain electrodes being connected with the pixel electrode [[on]] at an overlap of the source or drain electrodes and an end portion of the buffer layer;

forming a passivation layer on the pixel electrode; and

forming a common electrode on the passivation layer substantially parallel to the pixel electrode.

29. (Previously Presented) The method for manufacturing an in-plane switching mode LCD device as claimed in claim 28, wherein the gate electrode includes one of aluminum (Al), copper (Cu), and silver (Ag).

30. (Previously Presented) The method for manufacturing an in-plane switching mode LCD device as claimed in claim 28, wherein the buffer layer includes titanium (Ti).

31. (Previously Presented) The method for manufacturing an in-plane switching mode LCD device as claimed in claim 28, wherein the source and drain electrodes include one of aluminum (Al), copper (Cu), and silver (Ag).

32. (Previously Presented) The method for manufacturing an in-plane switching mode LCD device as claimed in claim 28, wherein the pixel electrode includes indium tin oxide.

33. (Previously Presented) The method for manufacturing an in-plane switching mode LCD device as claimed in claim 28, wherein the drain electrode is electrically connected with the pixel electrode.

34. (Previously Presented) The method for manufacturing an in-plane switching mode LCD device as claimed in claim 28, wherein the common electrode includes indium tin oxide.

35. (Previously Presented) The method for manufacturing an in-plane switching mode LCD device as claimed in claim 28, wherein the gate electrode is deposited by a sputtering process.

36. (Previously Presented) The method for manufacturing an in-plane switching mode LCD device as claimed in claim 35, wherein the gate electrode is patterned using photolithography.

37. (Previously Presented) The method for manufacturing an in-plane switching mode LCD device as claimed in claim 28, wherein the semiconductor layer, the ohmic contact layer, and the buffer layer are formed on the gate insulating film by a plasma enhanced chemical vapor deposition (PECVD) process.

38. (Previously Presented) The method for manufacturing an in-plane switching mode LCD device as claimed in claim 37, wherein the semiconductor layer, the ohmic contact layer, and the buffer layer are patterned.

39. (Previously Presented) The method for manufacturing an in-plane switching mode LCD device as claimed in claim 28, wherein the pixel electrode is formed by a sputtering process.

40. (Previously Presented) The method for manufacturing an in-plane switching mode LCD device as claimed in claim 39, wherein the pixel electrode is patterned.

41. (Previously Presented) The method for manufacturing an in-plane switching mode LCD device as claimed in claim 28, wherein the passivation layer is formed by a deposition process.